

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IPD60R750E6,IIPD60R750E6

FEATURES

- Static drain-source on-resistance: $R_{\text{DS}}(on){\leqslant}0.75\Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

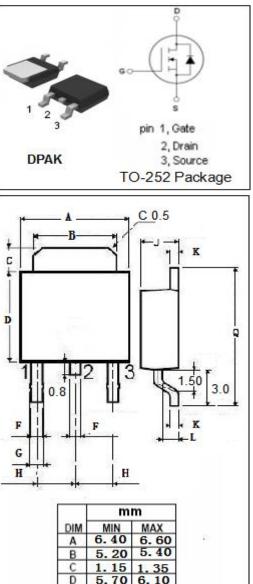
· High peak current capability

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C

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SYMBOL	PARAMETER	VALUE	UNIT			
V _{DSS}	Drain-Source Voltage	600	V			
V_{GS}	Gate-Source Voltage ±20		V			
ID	Drain Current-Continuous 5.7		A			
I _{DM}	Drain Current-Single Pulsed	15.7	А			
P _D	Total Dissipation @T _c =25°C	48	W			
Tj	Max. Operating Junction Temperature	150	°C			
T _{stg}	Storage Temperature	-55~150	Ĉ			

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT	
Rth(j-c)	Channel-to-case thermal resistance	2.6	°C/W	
Rth(j-a)	Channel-to-ambient thermal resistance	62	°C/W	



0.65

50

40

10

0.60

10

2.10

2.10

0.40

0.90

9.90

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0



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	600			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =0.17mA	2.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =2A			0.75	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V; V _{DS} =0V			0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			1	μA
V _{SD}	Diode forward voltage	I _F =2.5A, V _{GS} = 0V		0.9		V

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